

Amendments to the Claims:

1. (Currently amended) A test key layout, comprising:

5 a first test pattern substantially disposed at a center position of a test key area,
wherein said first test pattern consists of a pair of rectangular shaped symmetric patterns
having a length L and a width W, and wherein said test key area comprises a reference
X-Y coordinate;

a second test pattern arranged in proximity to said first test pattern in 45 degree
directions with respect to said first test pattern; ~~and~~

10 a third test pattern disposed next to said first test pattern along an X axis of said
reference X-Y coordinate; and

a fourth test pattern disposed a distance S_1 from said first test pattern along a Y-axis
of said reference X-Y coordinate.

~~wherein said first test pattern, said second test pattern, and said third test pattern are
15 arranged like a capital "H" within said test key area.~~

2. (Original) The test key layout of claim 1 wherein said test key layout is made on a
photomask comprising an array of deep-trench (DT) capacitor patterns, and wherein said
rectangular shaped symmetric patterns have a dimension that is substantial equal to
20 dimension of said DT capacitor patterns.

3. (Original) The test key layout of claim 1 wherein said test key layout is capable of
exclusively monitoring 3-foil aberration effect without affected by co-existed COMA
aberration effect.

25 4. (Canceled)

5. (Original) The test key layout of claim [[4]]1 wherein $S_1 = 3L$.

6. (Original) The test key layout of claim 1 wherein said second test pattern is disposed a distance S_2 from said third test pattern.

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7. (Original) The test key layout of claim 6 wherein $S_2 = L$.

8. (Original) The test key layout of claim 1 wherein said third test pattern is disposed a distance S_3 from said first test pattern.

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9. (Original) The test key layout of claim 8 wherein $S_3 = W$.